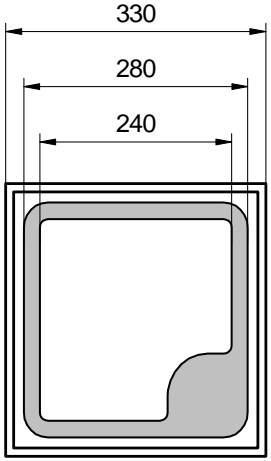


Radiation	Type	Technology	Electrodes
Infrared	DDH	AlGaAs/AlGaAs	P (anode) up

 <p style="text-align: center;">LED-23</p>	typ. dimensions (µm)	
	typ. thickness 180 µm anode gold alloy, 1.5 µm cathode gold alloy, 0.5 µm structured, 25% covered	

Optical and Electrical Characteristics

T_{amb} = 25°C, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	I _F = 20 mA	V _F		1.35	1.55	V
Reverse voltage	I _R = 100 µA	V _R	5			V
Radiant power ¹	I _F = 20 mA	Φ _e	3.5	5.0		mW
Radiant power ²	I _F = 20 mA	Φ _e		8.0		mW
Peak wavelength	I _F = 20 mA	λ _p	860	870	880	nm
Spectral bandwidth at 50%	I _F = 20 mA	Δλ _{0.5}		45		nm
Switching time	I _F = 20 mA	t _r , t _f		10/20		ns

¹Measured on bare chip on TO-18 header with JENOPTIK Polymer Systems equipment

²Measured on epoxy covered chip on TO-18 header with JENOPTIK Polymer Systems equipment

Labeling

Type	Lot N°	Φ _e (typ) [mW]	V _F (typ) [V]	Quantity
ELC-870-15-1				

Packing: Chips on adhesive film with wire-bond side on top